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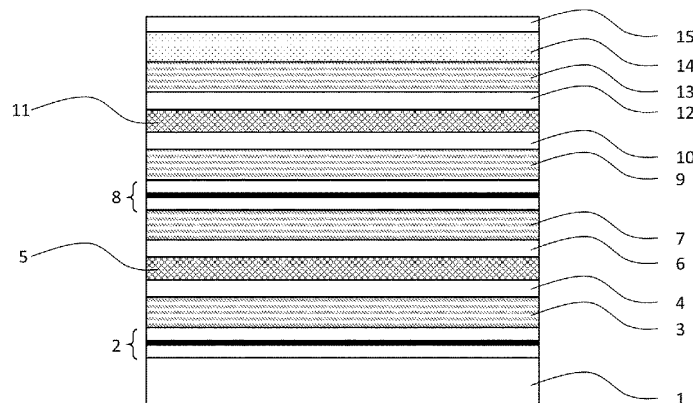


Fig. 1

(57) Abstract: The present invention concerns a glazing unit comprising a transparent substrate (1) provided with a stack of thin layers comprising in an alternating arrangement of only two infrared radiation reflecting functional layers, referred to starting from the substrate surface as first functional layer Ag1 (5) and second functional layer Ag2 (11) and 3 dielectric coatings, referred to starting from the substrate surface as D1, D2, and D3, such that each functional layer is surrounded by dielectric coatings, wherein the two functional layers comprise silver, and only D1 and D2 each comprise one layer of absorbing material and characterized in that: D1 comprises in sequence a bottom absorber layer sequence BA (2), in direct contact with the substrate, and a zinc oxide-comprising contact layer C1 (3), directly below and in contact with the overlying first functional layer Ag1 (5), D2 comprises in sequence a zinc oxide-comprising contact layer C2 (6), directly above and in contact with the underlying first functional layer Ag1 (5), a middle absorber layer sequence MA, a zinc oxide-comprising contact layer C3 (10), in contact with the second functional layer Ag2 (11), and D3 comprises in sequence a zinc oxide-comprising contact layer C4 (12), directly above and in contact with the underlying second functional layer Ag2 (11); further characterized in that BA (2) comprises a first layer of absorbing material AM1 inserted in a first silicon nitride comprising layer

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SiN1, and in that MA (2) comprises a second layer of absorbing material AM2 inserted in a second silicon nitride comprising layer SiN2.